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[JP/JP]; c/o Showa Denko K.K., 5-1, Yawata Kaigan dori, Ichihara-shi, Chiba, 2900067 (JP).

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(74) Agents: **AOKI, Atsushi** et al.; A. AOKI, ISHIDA & ASSOCIATES, Toranomom 37 Mori Bldg., 5-1, Toranomom 3-chome, Minato-ku, Tokyo 1058423 (JP).

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(71) Applicant (for all designated States except US): **SHOWA DENKO K.K.** [JP/JP]; 13-9, Shibadaimon 1-chome, Minato-ku, Tokyo, 1058518 (JP).

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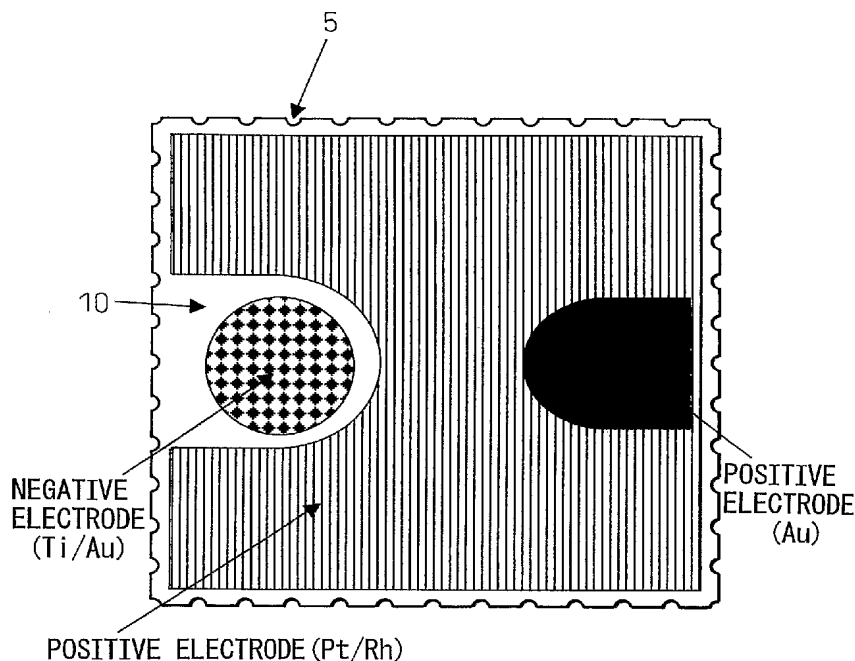
(72) Inventor; and

(75) Inventor/Applicant (for US only): **KUSUNOKI, Katsuki**

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(54) Title: COMPOUND SEMICONDUCTOR LIGHT-EMITTING DEVICE AND PRODUCTION METHOD THEREOF



(57) Abstract: An object of the present invention is to provide a compound semiconductor light-emitting device having side surfaces of large surface area to improve the efficiency for outwardly transmitting the emitted light. Another object of the present invention is to provide a technology capable of easily forming the side surfaces with large surface area without using a cutting tool and without the need of taking a trouble to impart mechanical damage. The inventive compound semiconductor light-emitting device has a light-emitting layer, on a substrate, wherein at least a part of a substrate portion of the device side surface has recessed portions in a side direction of the device. The inventive method of producing compound semiconductor light-emitting device comprises the steps of: (a) forming a compound semiconductor layer including a light-emitting layer of an n-type or p-type compound semiconductor on a wafer that serves

as a substrate, (b) arranging a negative electrode and a positive electrode at predetermined positions for passing a drive current through the light-emitting layer, (c) forming a separation zone for separating the individual light-emitting devices, (d) perforating many small holes linearly in the wafer that serves as the substrate along the separation zone, and (e) dividing the wafer into individual light-emitting devices along the separation zone.

WO 2005/091389 A1



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